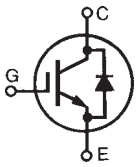
High Voltage, High Gain BIMOSFET™ Monolithic Bipolar MOS Transistor

IXBH 28N170A
IXBT 28N170A

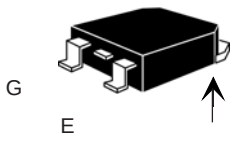
V_{CES} = 1700 V
I_{C25} = 30 A
$V_{CE(sat)}$ = 6.0 V
t_{fi} = 50 ns



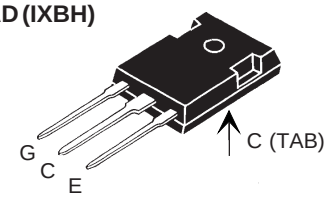
Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	1700	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	1700	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	30	A
I_{C90}	T_C = 90°C	14	A
I_{CM}	T_C = 25°C, 1 ms	60	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 10 Ω Clamped inductive load	I_{CM} = 60 V_{CES} = 1350	A V
P_C	T_C = 25°C	300	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
Maximum Lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
Maximum Tab temperature for soldering SMD devices for 10 s		260	°C
M_d	Mounting torque (M3) (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247 AD	6	g
	TO-268	4	g

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)		Characteristic Values min.	typ.	max.	
BV_{CES}	I_C = 250 µA, V_{GE} = 0 V		1700			V
	Temperature Coefficent			0.10		%/K
$V_{GE(th)}$	I_C = 250 µA, V_{CE} = V_{GE}		3.0		6.0	V
	Temperature Coefficent			- 0.24		%/K
I_{CES}	V_{CE} = 0.8 V_{CES}	T_J = 25°C			10	µA
	V_{GE} = 0 V	T_J = 125°C			100	µA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}, V_{GE} = 15 V			4.7	6.0	V
		T_J = 125°C		5.0		V

TO-268 (IXBT)



TO-247 AD (IXBH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- High Blocking Voltage
- JEDEC TO-268 surface and JEDEC TO-247 AD
- Low conduction losses
- High current handling capability
- MOS Gate turn-on
  - drive simplicity
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- AC motor speed control
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- Capacitor discharge circuits

Advantages

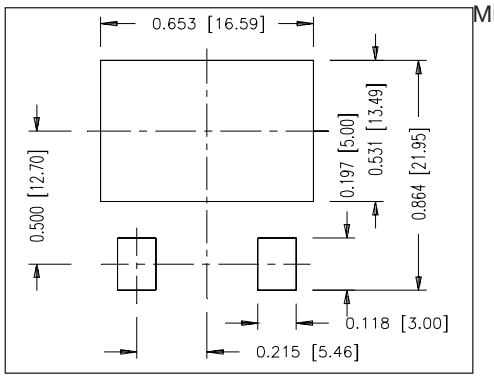
- High power density
- Suitable for surface mounting
- Easy to mount with 1 screw, (isolated mounting screw hole)

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Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %	12	17		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		2800		pF
C_{oes}			132		pF
C_{res}			42		pF
Q_g	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		105		nC
Q_{ge}			20		nC
Q_{gc}			35		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C** $I_C = I_{C90}$, V_{GE} = 15 V V_{CE} = 850 V, $R_G = R_{off}$ = 10 Ω		35		ns
t_{ri}			36		ns
$t_{d(off)}$			265		ns
t_{fi}			50		ns
E_{off}			1.2		mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C** $I_C = I_{C90}$, V_{GE} = 15 V V_{CE} = 850 V, $R_G = R_{off}$ = 10 Ω		35		ns
t_{ri}			36		ns
E_{on}			0.7		mJ
$t_{d(off)}$			290		ns
t_{fi}			150		ns
E_{off}			2.3		mJ
R_{thJC}				0.42	K/W
R_{thCK}	(TO-247)		0.25		K/W

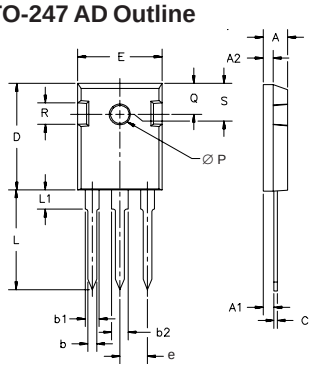
Reverse Diode

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values min.	typ.	max.	
V_F	$I_F = I_{C90}$, V_{GE} = 0 V, Pulse test, t ≤ 300 us, duty cycle d ≤ 2%			3.0	V
I_{RM}	$I_F = I_{C90}$, V_{GE} = 0 V, $-di_F/dt$ = 50 A/us		25		A
t_{rr}	v_R = 100 V		360		ns



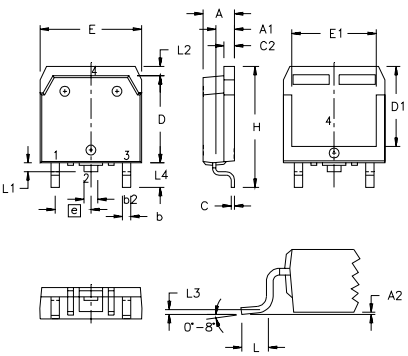
Min Recommended Footprint

TO-247 AD Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A_1	2.2	2.54	.087	.102
A_2	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b_1	1.65	2.13	.065	.084
b_2	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15 BSC		242 BSC	

TO-268 Outline



SYM	INCHES MIN	MAX	MILLIMETERS MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343